

P375-7722B

UV LED Array

P375-7722B is designed for UV LED illuminating high power source.
It is composed of 1mm*1mm high power UV die by 24pcs mounted on copper substrate as direct bonding with silver plated reflector and is covered by silicone resin.
Total output power is 2.5W at 375nm.

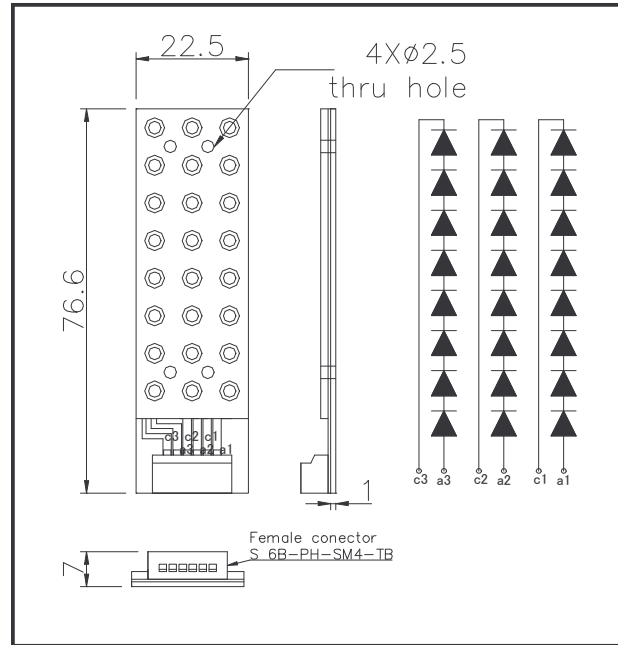
◆ Features

- 1) High output power at 375nm
- 2) High heat dispersion PCB
- 3) High current drive

◆ Specifications

- 1) Product name UVLED Source
- 2) Spec. No. P375-7722B
- 3) Chip
 - (1) Material InGaN
 - (2) Peak wavelength 375nm
- 4) Package
 - (1) Package(PCB) Cu (t=1mm)
 - (2) Lens Silicone Resin

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	70	W	T _a =25°C
Forward Current	I _F	750mA x 3Line	mA	T _a =25°C
Reverse Voltage	V _R	20	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Soldering condition : Soldering condition must be completed within 3 seconds at 265°C

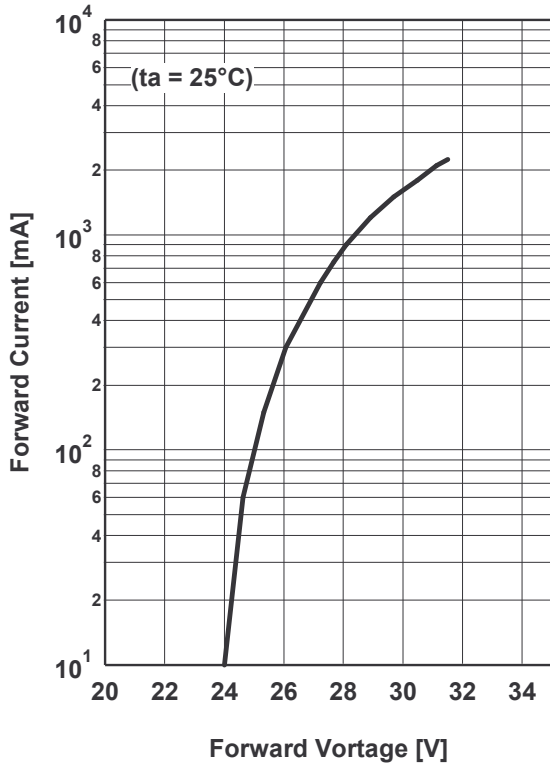
◆ Electro-Optical Characteristics (500mA/each line)

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =3*500mA		30		V
Brightness	I _v	I _F =3*500mA		-		mcd
Total Radiated Power	P _O	I _F =3*500mA		2500		mW
Radiant Intensity	I _E	I _F =3*500mA		-		mW/sr
Reverse Current	V _R	I _R =10uA	20			V
Peak Wavelength	λ _P	I _F =3*500mA	370	375	380	nm
Half Width	Δλ	I _F =3*500mA		17		nm

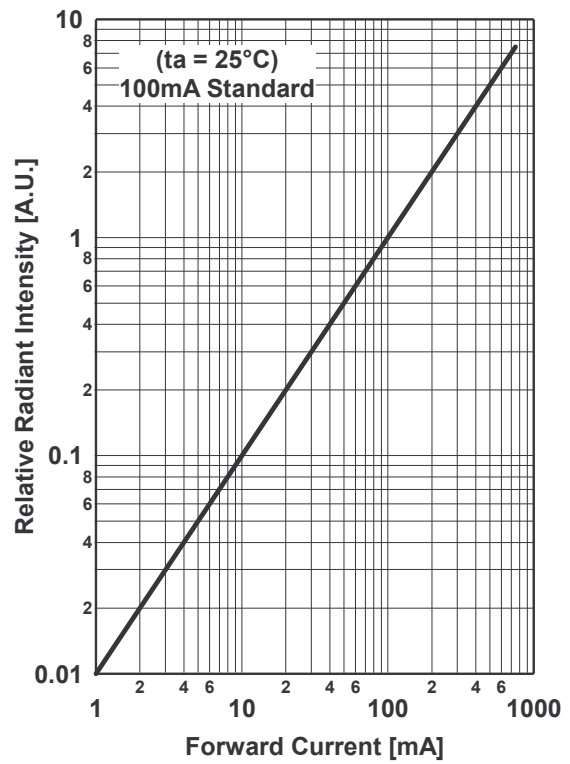
‡Heat sink is required to protect LED at 60°C or less.

‡Total Radiated Power is measured by S3584-08

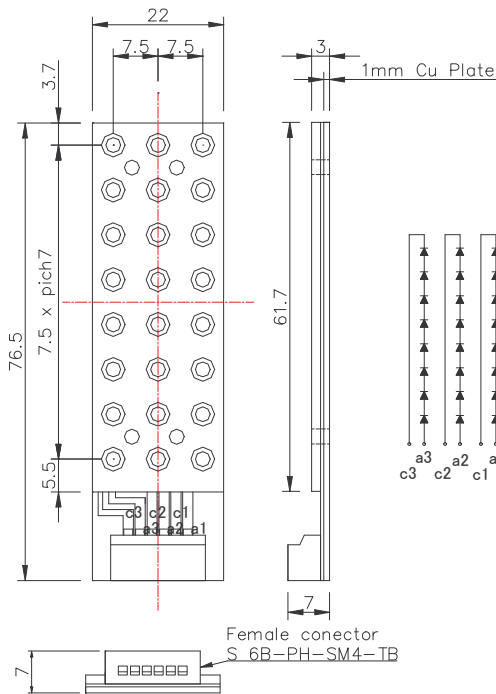
**Forward Current
V.S. Forward Voltage**



**Relative Radiant Intensity
V.S. Forward Current**



Outer Dimension and Light Point Pitch



Outer Dimension and Through hole Pitch

